

NP100P06PLG

-60V – -100A – P-channel Power MOS FET

R07DS1522EJ0100

Rev.1.00

Application : Automotive

Jun. 24, 2022

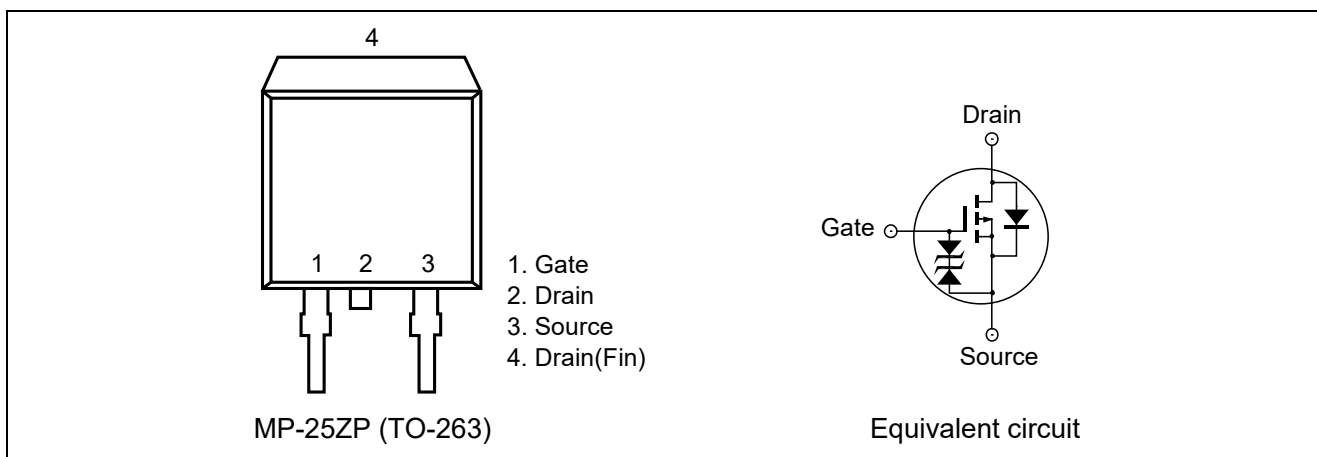
Description

This product is P-channel MOS Field Effect Transistor designed for high current switching applications.

Features

- Super low on-state resistance : $R_{DS(on)} = 6.0 \text{ m}\Omega \text{ Max.}$ ($V_{GS} = -10 \text{ V}$, $I_D = -50 \text{ A}$)
 $R_{DS(on)} = 7.8 \text{ m}\Omega \text{ Max.}$ ($V_{GS} = -4.5 \text{ V}$, $I_D = -50 \text{ A}$)
- Low input capacitance : $C_{iss} = 15000 \text{ pF Typ.}$
- Built-in gate protection diode
- Designed for automotive application and AEC-Q101 qualified.
- Pb-free (This product does not contain Pb in the external electrode)

Outline



Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	-60	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_c = 25^\circ\text{C}$)	$I_{D(DC)}$	± 100	A
Drain Current (pulse)	$I_{D(pulse)}$ Notes1	± 300	A
Total Power Dissipation ($T_c = 25^\circ\text{C}$)	P_{T1}	200	W
Total Power Dissipation ($T_a = 25^\circ\text{C}$)	P_{T2}	1.8	W
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 175	$^\circ\text{C}$
Single Avalanche Current	I_{AS} Notes2	64	A
Single Avalanche Energy	E_{AS} Notes2	420	mJ

Notes 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

2. Starting $T_{ch} = 25^\circ\text{C}$, $V_{DD} = -30\text{V}$, $R_G = 25 \Omega$, $V_{GS} = -20 \rightarrow 0\text{V}$, $L = 100\mu\text{H}$

Thermal Resistance

Channel to Case Thermal Resistance	$R_{th(ch-c)}$ ^{Notes3}	0.75	°C/W
Channel to Ambient Thermal Resistance	$R_{th(ch-a)}$ ^{Notes3}	83.3	°C/W

Electrical Characteristics

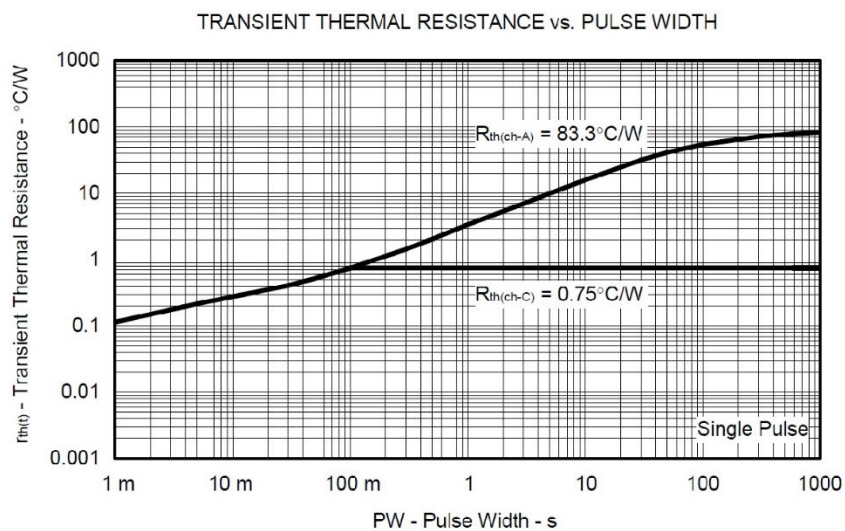
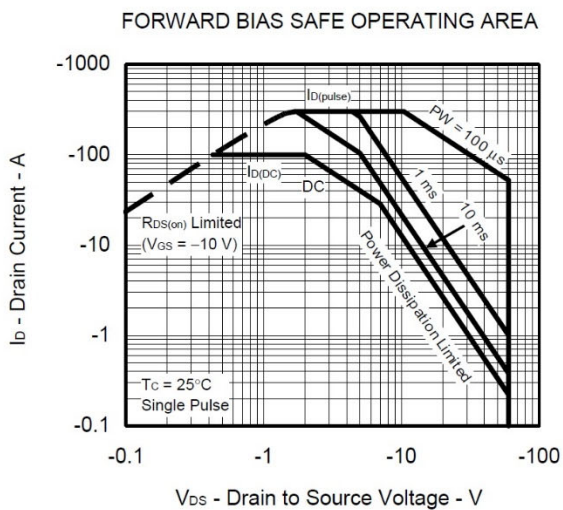
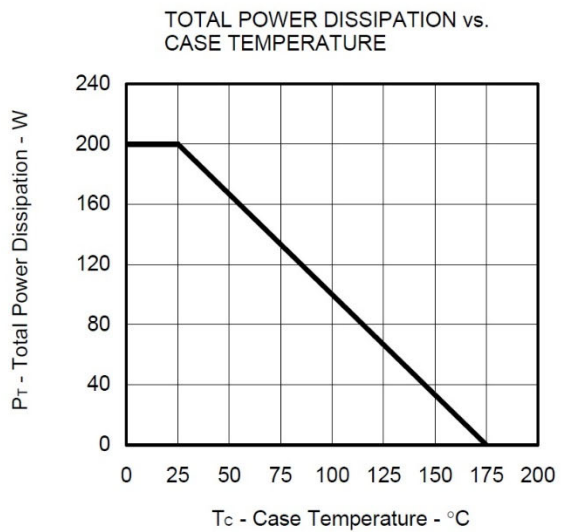
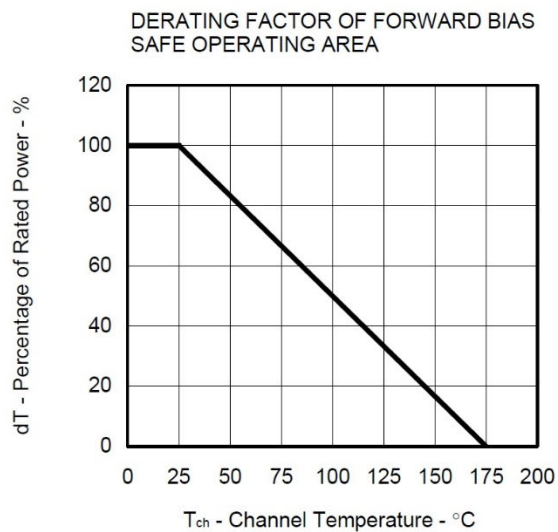
(T_a=25°C)

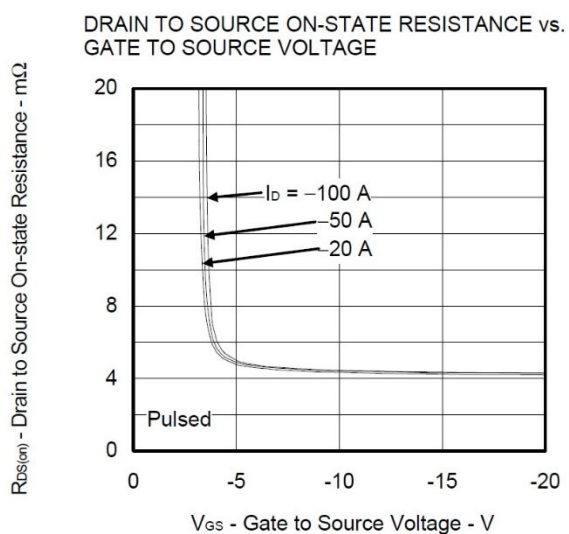
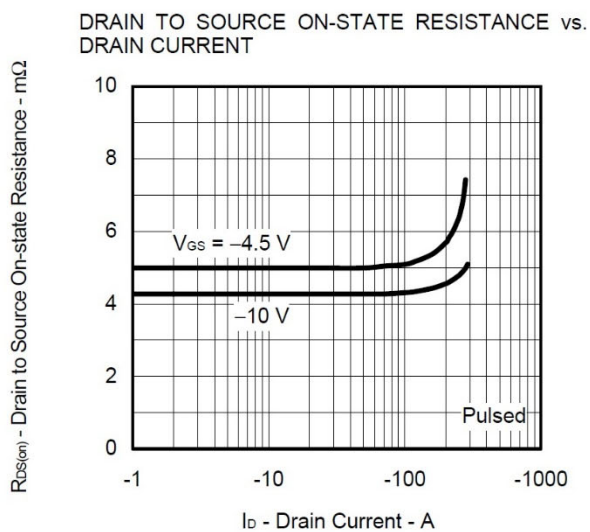
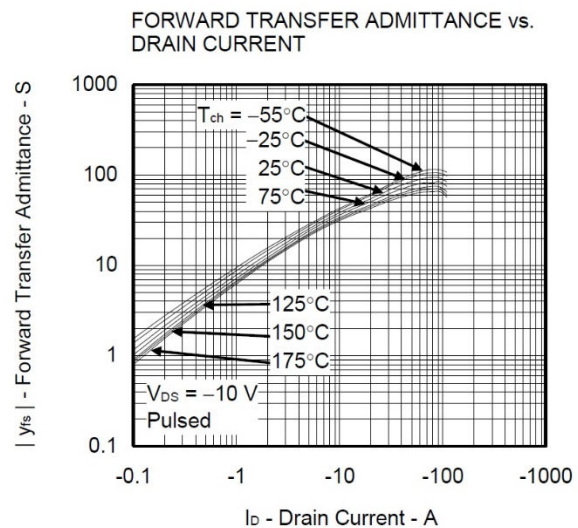
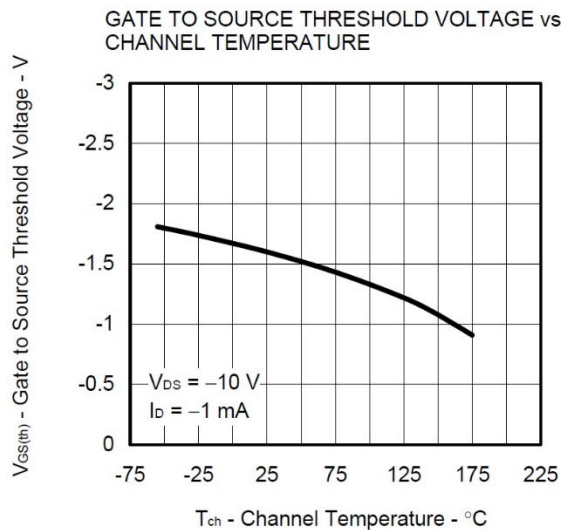
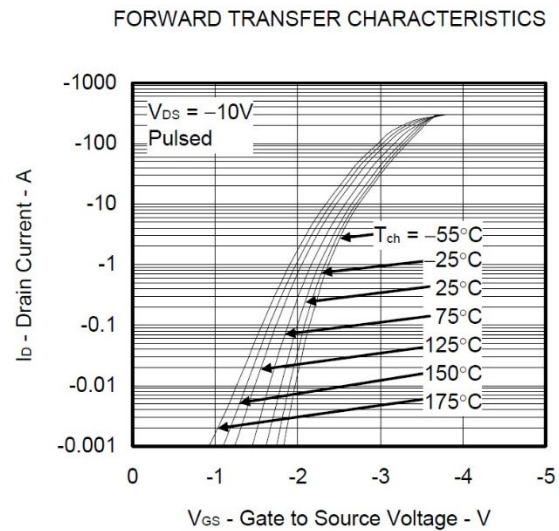
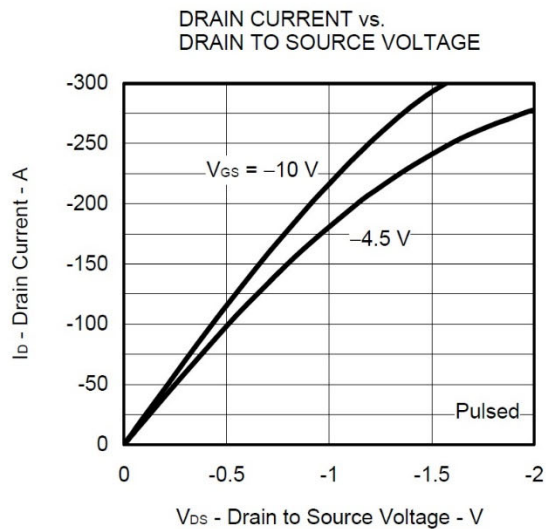
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-10	μA	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$
Gate Leakage Current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$
Gate to Source Threshold Voltage	$V_{GS(th)}$	-1.0	-1.6	-2.5	V	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$
Forward Transfer Admittance	$ y_{fs} $ ^{Notes4}	43	86	—	S	$V_{DS} = -10\text{ V}, I_D = -50\text{ A}$
Drain to Source On-state Resistance	$R_{DS(on)1}$ ^{Notes4}	—	4.4	6.0	mΩ	$V_{GS} = -10\text{ V}, I_D = -50\text{ A}$
	$R_{DS(on)2}$ ^{Notes4}	—	5.0	7.8	mΩ	$V_{GS} = -4.5\text{ V}, I_D = -50\text{ A}$
Input Capacitance	C_{iss}	—	15000	—	pF	$V_{DS} = -10\text{ V}$
Output Capacitance	C_{oss}	—	1810	—	pF	$V_{GS} = 0\text{ V}$
Reverse Transfer Capacitance	C_{rss}	—	840	—	pF	$f = 1\text{ MHz}$
Turn-on Delay Time	$t_{d(on)}$	—	28	—	ns	$V_{DD} = -30\text{ V}$
Rise Time	t_r	—	35	—	ns	$I_D = -50\text{ A}$
Turn-off Delay Time	$t_{d(off)}$	—	275	—	ns	$V_{GS} = -10\text{ V}$
Fall Time	t_f	—	100	—	ns	$R_G = 0\text{ }\Omega$
Total Gate Charge	Q_g	—	300	—	nC	$V_{DD} = -48\text{ V}$
Gate to Source Charge	Q_{gs}	—	35	—	nC	$V_{GS} = -10\text{ V}$
Gate to Drain Charge	Q_{gd}	—	85	—	nC	$I_D = -100\text{ A}$
Body Diode Forward Voltage	$V_{F(S-D)}$ ^{Notes4}	—	0.92	1.5	V	$I_F = -100\text{ A}, V_{GS} = 0\text{ V}$
Reverse Recovery Time	t_{rr}	—	70	—	ns	$I_F = -100\text{ A}, V_{GS} = 0\text{ V}$
Reverse Recovery Charge	Q_{rr}	—	135	—	nC	$di/dt = -100\text{ A}/\mu\text{s}$

Notes 3. Designed target value on Renesas measurement condition. Not subject to production test.

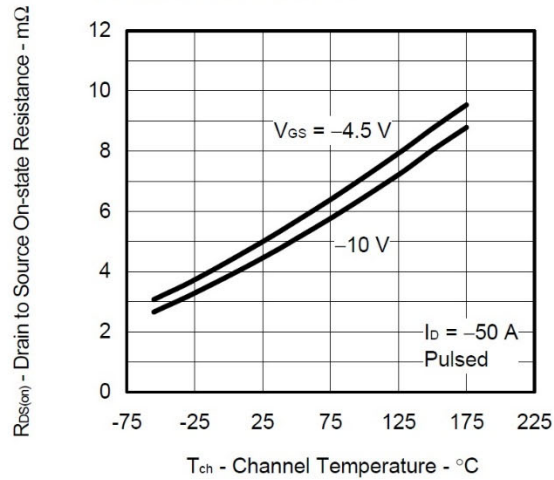
4. Pulse test.

Typical Characteristics

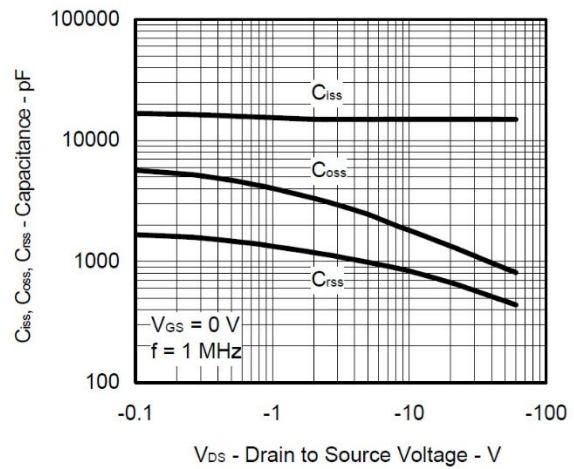




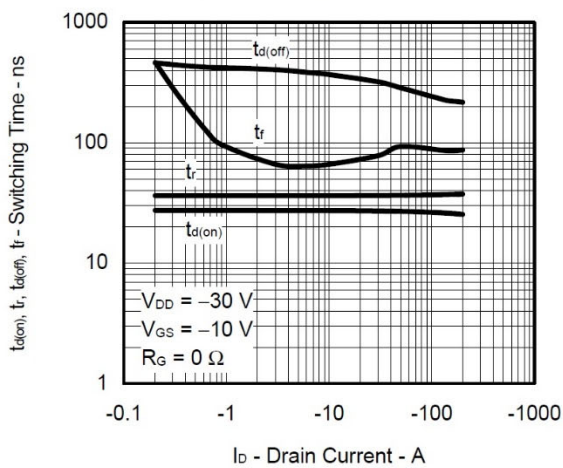
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



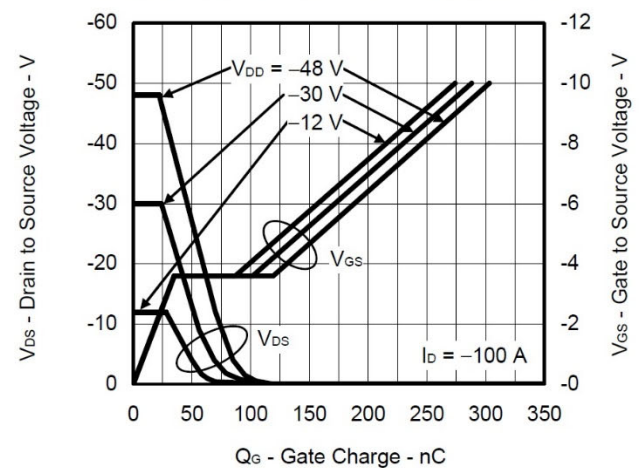
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



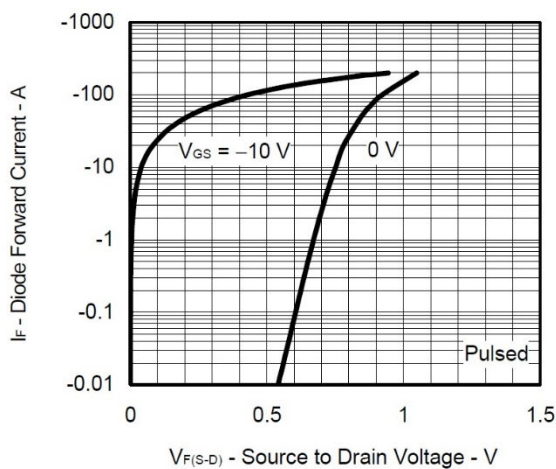
SWITCHING CHARACTERISTICS



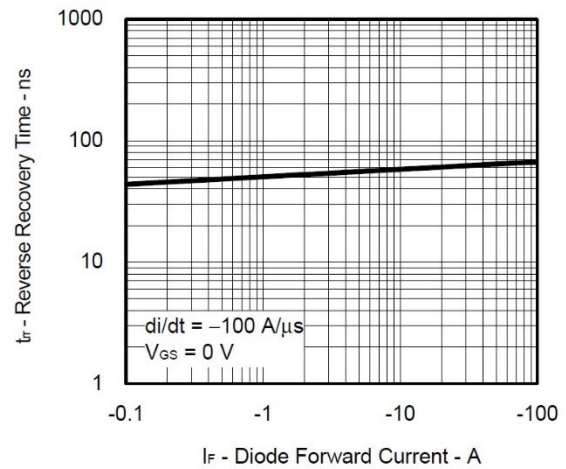
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



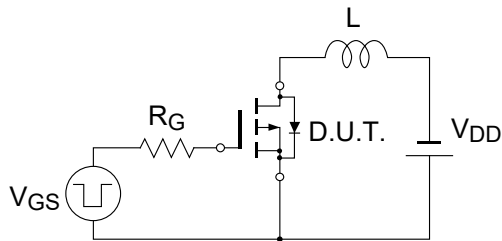
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



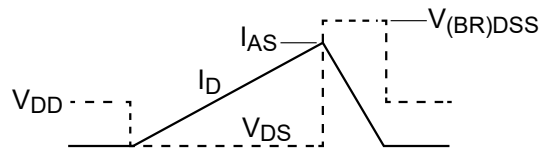
Test Circuit

Avalanche

Test Circuit



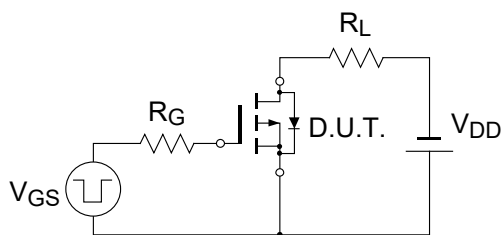
Waveform



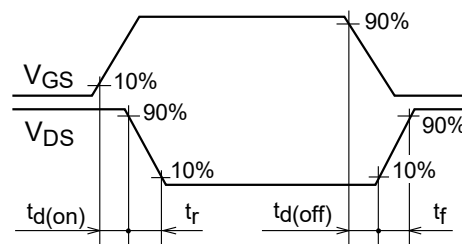
$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AS}^2 \cdot \frac{V_{(BR)DSS}}{V_{(BR)DSS} - V_{DD}}$$

Switching Time

Test Circuit

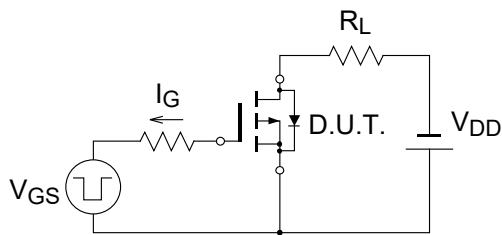


Waveform

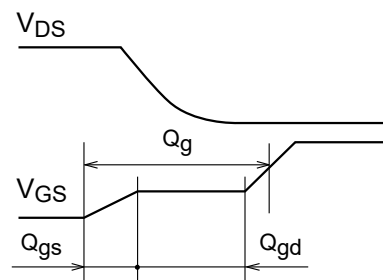


Gate Charge

Test Circuit

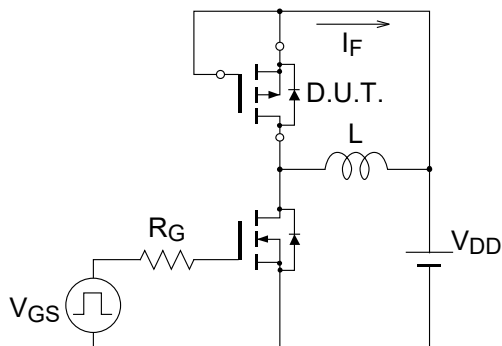


Waveform

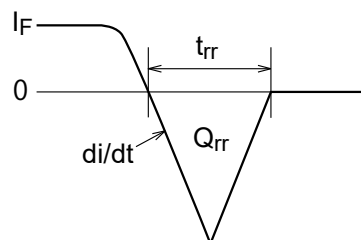


Reverse Recovery

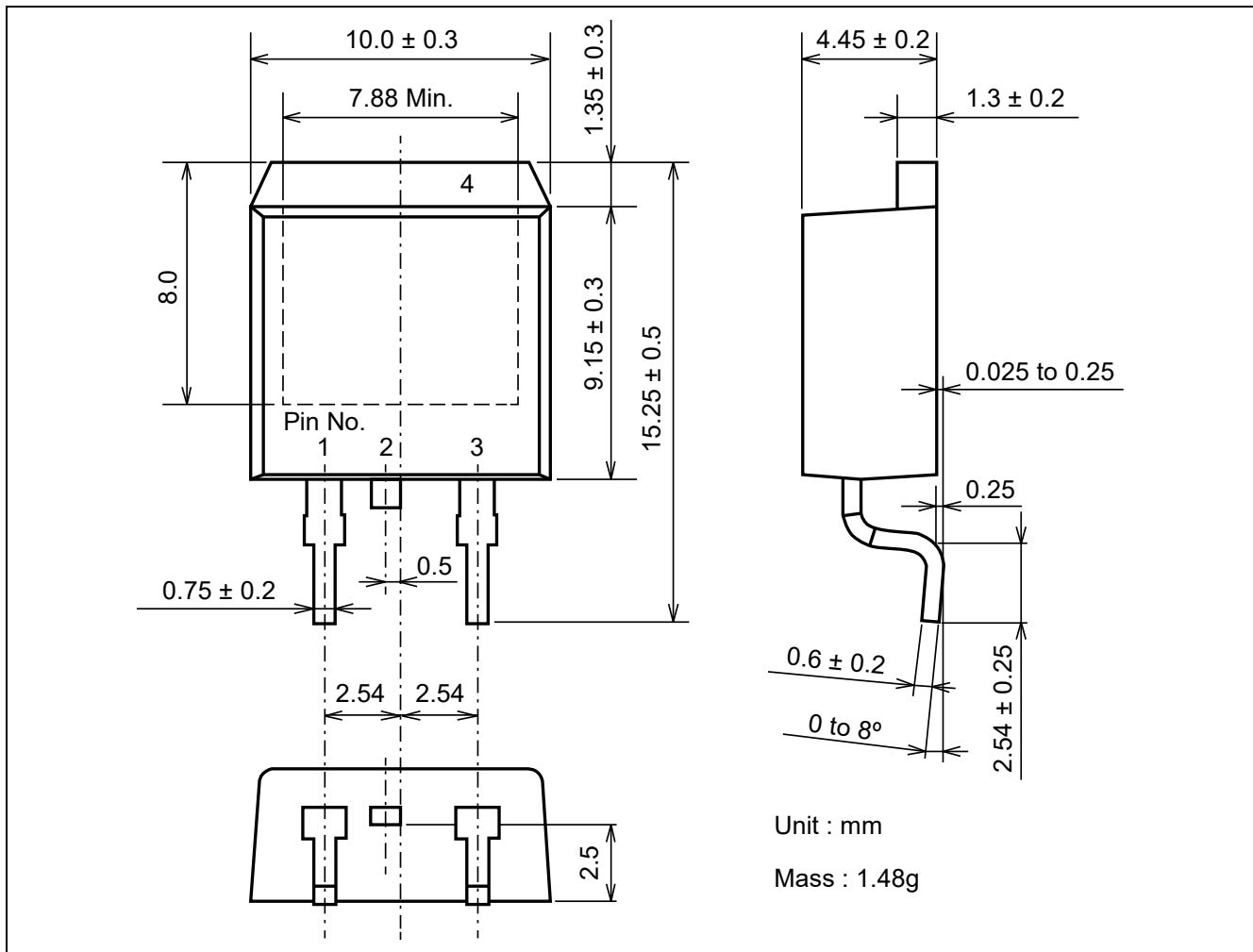
Test Circuit



Waveform



Package Dimensions



Ordering Information

Part No.	Quantity	Shipping container
NP100P06PLG-E1-AY	800pcs/reel	Taping

Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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